

CW lasing of current injection blue GaN-based vertical c

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Citation Report

#	ARTICLE	IF	CITATIONS
1	High-reflectivity ultraviolet AlN/AlGa _N distributed Bragg reflectors grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2008, 310, 4871-4875.	0.7	11
2	Room temperature polariton lasing in a GaN/AlGa _N multiple quantum well microcavity. Applied Physics Letters, 2008, 93, .	1.5	267
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5	Room-Temperature CW Lasing of a GaN-Based Vertical-Cavity Surface-Emitting Laser by Current Injection. Applied Physics Express, 0, 1, 121102.	1.1	151
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